

Receipt date: 05/30/2006

/DN/

10581127 - GAU: 2895

Sheet 1 of 2

AP20 Rec'd PCT/PTO 30 MAY 2006

FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT				ATTY DOCKET NO. 536-009.028		SERIAL NO. To be assigned 10/581127			
				APPLICANT: B. HEINEMANN et al.					
				FILING DATE: Herewith		ART UNIT: To be assigned D. Nhu			
UNITED STATES PATENT DOCUMENTS									
EXAM. INITIAL		DOCUMENT NUMBER	DATE	INVENTOR/ASSIGNEE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE		
/DN/		2005/0023642	Feb. 03, 2005	Heinemann et al.					
		2003/0146477	Aug. 07, 2003	Krutsick					
		2003/0146468	Aug. 07, 2003	Gris et al.					
		2002/0168829	Nov. 14, 2002	Bock et al.					
/DN/		2003/0162360	Aug. 28, 2003	Beasom					
FOREIGN PATENT DOCUMENTS									
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO		
/DN/		EP 0 746 038	Dec. 19, 2001	EP					
/DN/		2000188296	July 04, 2000	JP					
/DN/		2000269350	Sept. 29, 2000	JP					
OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)									
/DN/	1	M. C. Wilson et al., "Process HJ: A 30 GHz NPN and 20 GHz PNP complementary bipolar process for high linearity RF circuits," IEEE BCTM 9.4, 1998, pp.164-167.							
	2	D. Knoll et al., "A flexible, low-cost, high performance SiGe:C BiCMOS process with a one-mask HBT module," IEEE, 2002.							
	3	B. Heinemann et al., "Novel collector design for high-speed SiGe:C HBTs," IEEE, 2002.							
	4	D. V. Singh et al., "Novel epitaxial p-Si/n-Si _{1-y} C _y /p-Si heterojunction bipolar transistors," IEEE, 2000.							
	5	B. El-Kareh et al., "A 5V complementary -SiGe BiCMOS technology for high-speed precision analog circuits." Date unknown							
/DN/	6	D. V. Singh et al., "Effect of band alignment and density of states on the collector current in p-Si/n-Si _{1-y} C _y /p-Si HBTs," IEEE Transactions on Electron Devices, Vol. 50, No. 2, February 2003, pp. 425-32.							
Examiner (To be assigned) /David Nhu/				Date: 09/02/2010					

FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT			ATTY DOCKET NO. 536-009.028		SERIAL NO. 10/581127 To be assigned		
			APPLICANT: B. HEINEMANN et al.				
			FILING DATE: Herewith		ART UNIT: D. Nhu To be assigned		
UNITED STATES PATENT DOCUMENTS							
EXAM. INITIAL		DOCUMENT NUMBER	DATE	INVENTOR/ASSIGNEE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
/DN/		2003/0219952	Nov. 27, 2003	Fujimaki			
/DN/		6,222,250	April 24, 2001	Gomi			
/DN/		4,719,185	Jan. 12, 1988	Goth			
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO
OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)							
/DN/	7	Y. Chyan et al., "A 50-GHz 0.25 μ m implanted-base high-energy implanted-collector complementary modular BiCMOS (HEICBiC) technology for low-power wireless-communication VLSIs," IEEE BCTM 7.3, 1998, pp. 128-131. Date unknown					
	8	D. L. Harame et al., "55 GHz polysilicon-emitter graded SiGe-base PNP transistors," 1991, p. 71.					
	9	T. Onai et al., "Self-aligned complementary bipolar technology for low-power dissipation and ultra-high-speed LSIs," IEEE Transactions on Electron Devices, Vol. 42, No. 3, March 1995, pp. 413-418.					
	10	S. J. Jeng et al., "A 210-GHz <i>f_T</i> SiGe HBT with a non-self-aligned structure," IEEE Electron Device Letters, Vol. 22, No. 11, November 2001.					
	11	J. D. Cressler et al., "A high-speed complementary silicon bipolar technology with 12-fJ power-delay product," IEEE Electron Device Letters, Vol. 14, No. 11, November 1993, pp. 523-526.					
/DN/	12	W. Klein et al., "75 GHz bipolar production technology for the 21st century," pp. 88-94. Date unknown					
Examiner (To be assigned) /David Nhu/				Date: 09/02/2010			